



# SPN166T06

## N-Channel Enhancement Mode MOSFET

### DESCRIPTION

The SPN166T06 is the N-Channel logic enhancement mode power field effect transistor which is produced using super high cell density DMOS trench technology. This high density process is especially tailored to minimize on-state resistance. These devices are particularly suitable for synchronous rectifier application, Motor control power management and other Power Tool circuits. It has been optimized for low gate charge, low  $R_{DS(ON)}$  and fast switching speed.

### APPLICATIONS

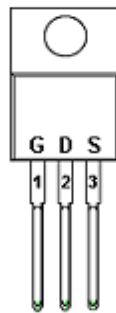
- DC/DC Converter
- Load Switch
- SMPS Secondary Side Synchronous Rectifier
- Motor Control
- Power Tool

### FEATURES

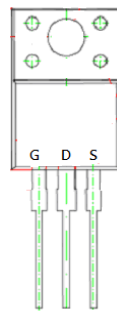
- ◆ 60V/166A,  $R_{DS(ON)}=3.0m\Omega@V_{GS}=10V$   
 $R_{DS(ON)}=4.5m\Omega@V_{GS}=4.5V$
- ◆ Super high density cell design for extremely low  $R_{DS(ON)}$
- ◆ Exceptional on-resistance and maximum DC current capability
- ◆ TO-220-3L/TO-220F-3L/PPAK5x6-8L package design

### PIN CONFIGURATION

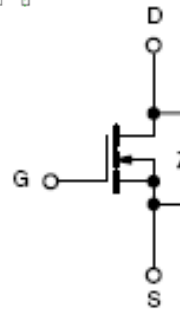
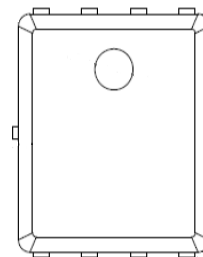
TO-220



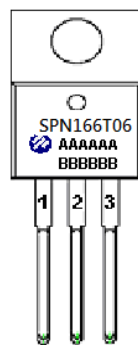
TO-220F



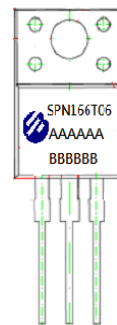
PPAK 5x6



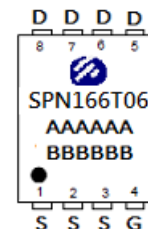
### PART MARKING



A : Lot Code  
B : Date Code  
(YY/MM/DD)



A: Lot Code  
B: Date Code  
(YYMMDD)



A : Lot Code  
B : Date Code  
(YY/MM/DD)



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## N-Channel Enhancement Mode MOSFET

### PIN DESCRIPTION

Pin	Symbol	Description
1	G	Gate
2	D	Drain
3	S	Source

### PPAK5x6 PIN DESCRIPTION

Pin	Symbol	Description
1	S	Source
2	S	Source
3	S	Source
4	G	Gate
5	D	Drain
6	D	Drain
7	D	Drain
8	D	Drain

### ORDERING INFORMATION

Part Number	Package	Part Marking
SPN166T06T220TGB	TO-220-3L	SPN166T06
SPN166T06T220FTGB	TO-220F-3L	SPN166T06
SPN166T06DN8RGB	PPAK5x6-8L	SPN166T06

- ※ SPN166T06T220TGB : Tube ; Pb – Free ; Halogen – Free
- ※ SPN166T06T220FTGB : Tube ; Pb – Free ; Halogen – Free
- ※ SPN166T06DN8RGB : Tape&Reel ; Pb – Free ; Halogen - Free



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### ABSOLUTE MAXIMUM RATINGS

(TA=25°C Unless otherwise noted)

Parameter	Symbol	Typical	Unit	
Drain-Source Voltage	V <sub>DSS</sub>	60	V	
Gate –Source Voltage	V <sub>GSS</sub>	±20	V	
Continuous Drain Current (Silicon Limited)(TO-220/TO-220F)	I <sub>D</sub>	Tc=25°C	166	A
		Tc=70°C	118	
Continuous Drain Current (Silicon Limited)(PPAK5x6)	I <sub>D</sub>	Tc=25°C	161	A
		Tc=70°C	102	
Pulsed Drain Current	I <sub>DM</sub>	400	A	
Power Dissipation @ Tc=25°C	P <sub>D</sub>	TO-220	104	W
Power Dissipation @ Tc=25°C		TO-220F	93	
Power Dissipation @ Tc=25°C		PPAK5x6	83	
Avalanche Energy with Single Pulse ( Tc=25°C , L=0.1mH. )	EAS	73	mJ	
Operating Junction Temperature	T <sub>J</sub>	-55/150	°C	
Storage Temperature Range	T <sub>STG</sub>	-55/150	°C	
Thermal Resistance-Junction to Case (TO-220/TO-220F)	R <sub>θJC</sub>	1.2	°C/W	
Thermal Resistance-Junction to Case (PPAK5x6)	R <sub>θJC</sub>	1.5	°C/W	

#### Note :

The maximum current rating is package limited at 78A for TO-220F-3L

The maximum current rating is package limited at 80A for PPAK5x6-8L



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### ELECTRICAL CHARACTERISTICS

(TA=25°C Unless otherwise noted)

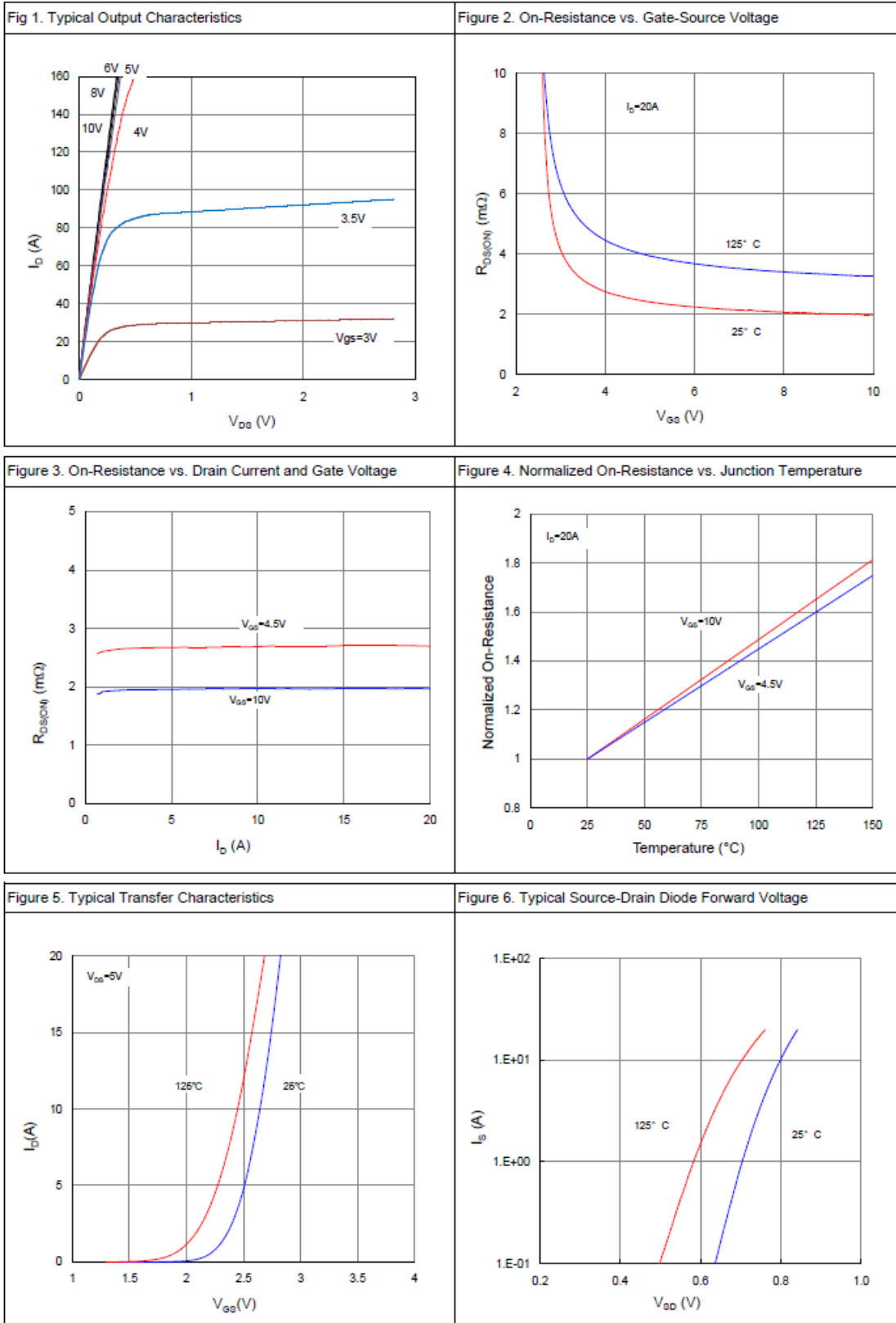
Parameter	Symbol	Conditions	Min.	Typ	Max.	Unit
<b>Static</b>						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS}=0V, I_D=250\mu A$	60			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	1.0	1.6	2.4	
Gate Leakage Current	$I_{GSS}$	$V_{DS}=0V, V_{GS}=\pm 20V$			$\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=48V, V_{GS}=0V$ $T_J=25^\circ C$			1	uA
		$V_{DS}=48V, V_{GS}=0V$ $T_J=100^\circ C$			100	
Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=20A$		2.5	3.0	mΩ
		$V_{GS}=4.5V, I_D=20A$		3.5	4.5	
Forward Transconductance	$g_{fs}$	$V_{DS}=5V, I_D=20A$		80		S
Diode Forward Voltage	$V_{SD}$	$I_S=20A, V_{GS}=0V$		0.9	1.2	V
Gate Resistance	$R_G$	$V_{GS}=0V, V_{DS}$ open, $f=1MHz$		1.6		Ω
<b>Dynamic</b>						
Total Gate Charge (10V)	$Q_g$	$V_{DS}=30V, V_{GS}=10V$ $I_D=20A$		64		nC
Total Gate Charge (4.5V)	$Q_g$			31		
Gate-Source Charge	$Q_{gs}$			18		
Gate-Drain Charge	$Q_{gd}$			12		
Input Capacitance	$C_{iss}$	$V_{DS}=30V, V_{GS}=0V$ $f=1MHz$		4424		pF
Output Capacitance	$C_{oss}$			1670		
Reverse Transfer Capacitance	$C_{rss}$			73		
Turn-On Time	$t_{d(on)}$	$V_{DD}=30V, I_D=20A$ $V_{GEN}=10V, R_G=10\Omega$		14		nS
	$t_r$			11		
Turn-Off Time	$t_{d(off)}$			58		
	$t_f$			17		



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### TYPICAL CHARACTERISTICS





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### TYPICAL CHARACTERISTICS

Figure 7. Typical Gate-Charge vs. Gate-to-Source Voltage

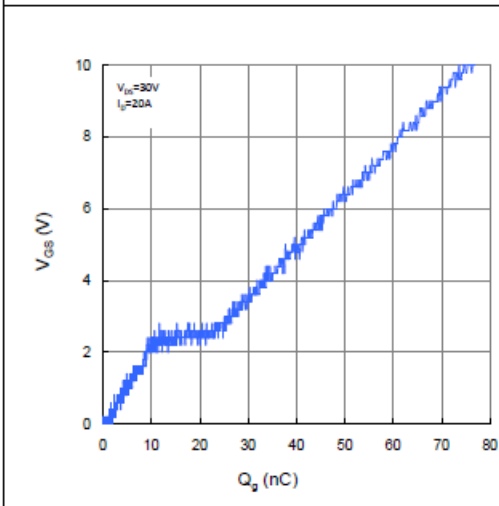


Figure 8. Typical Capacitance vs. Drain-to-Source Voltage

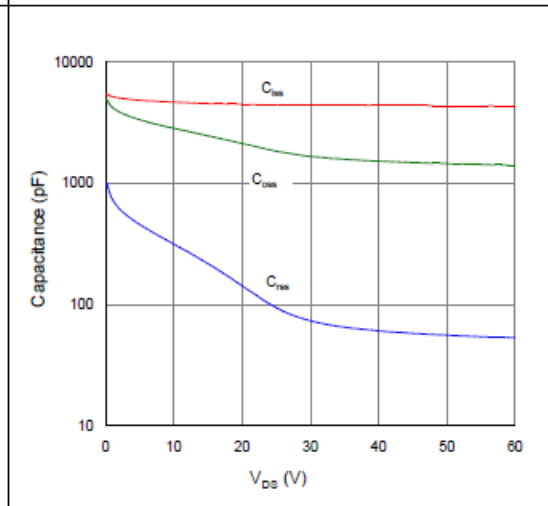


Figure 9. Maximum Safe Operating Area

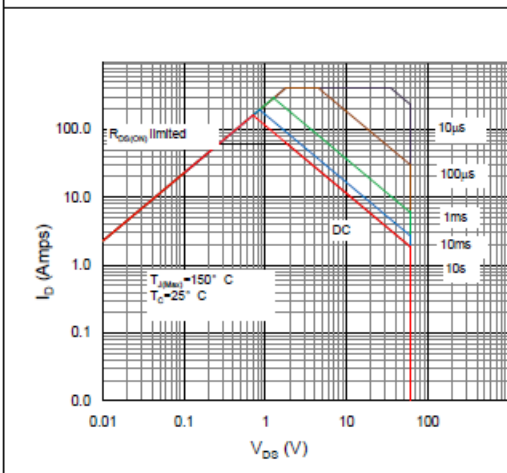


Figure 10. Maximum Drain Current vs. Case Temperature

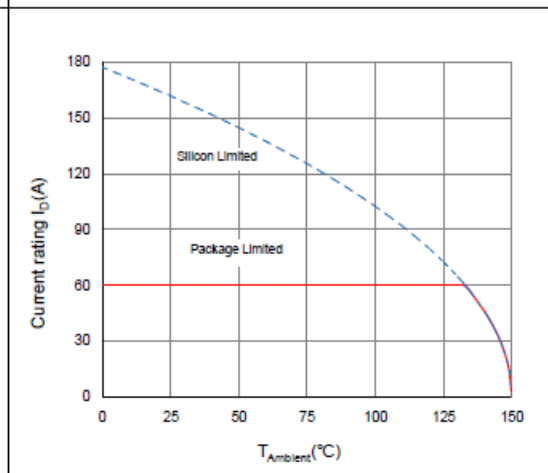
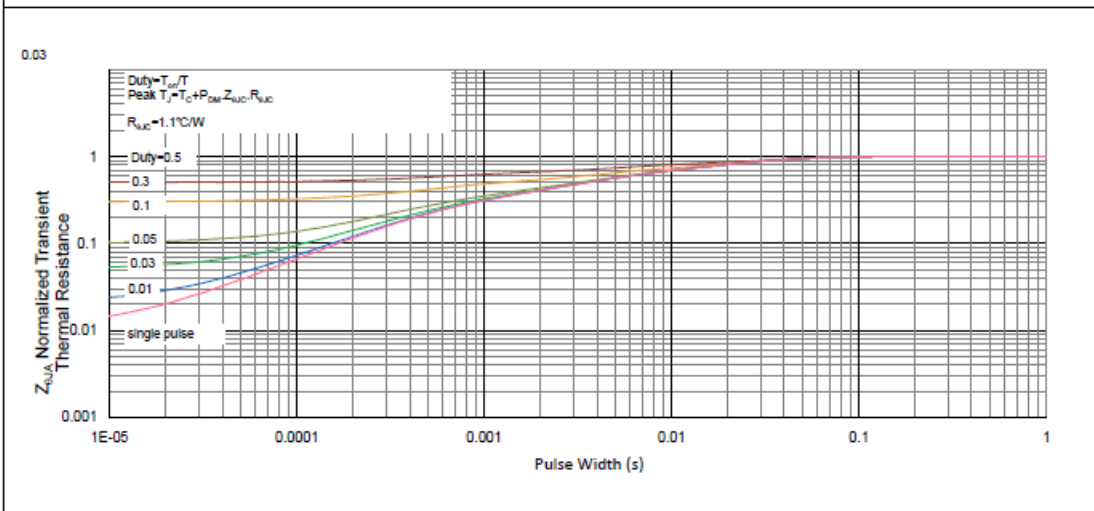


Figure 11. Normalized Maximum Transient Thermal Impedance, Junction-to-Ambient

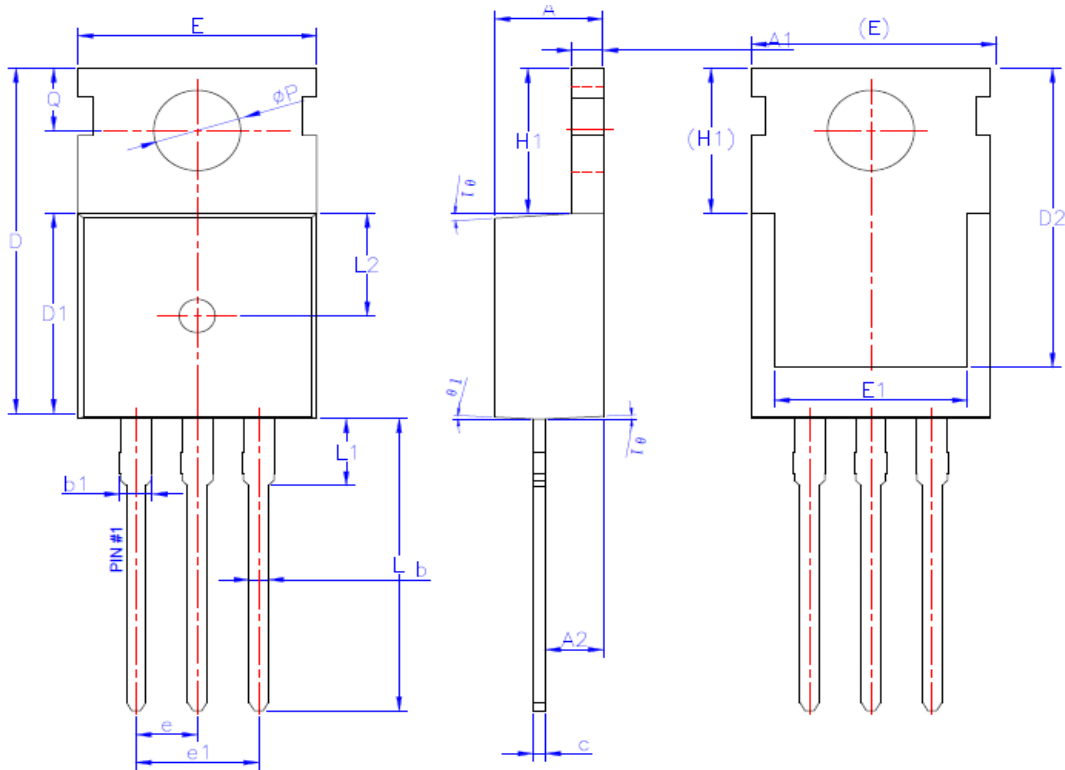




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### TO-220-3L PACKAGE OUTLINE



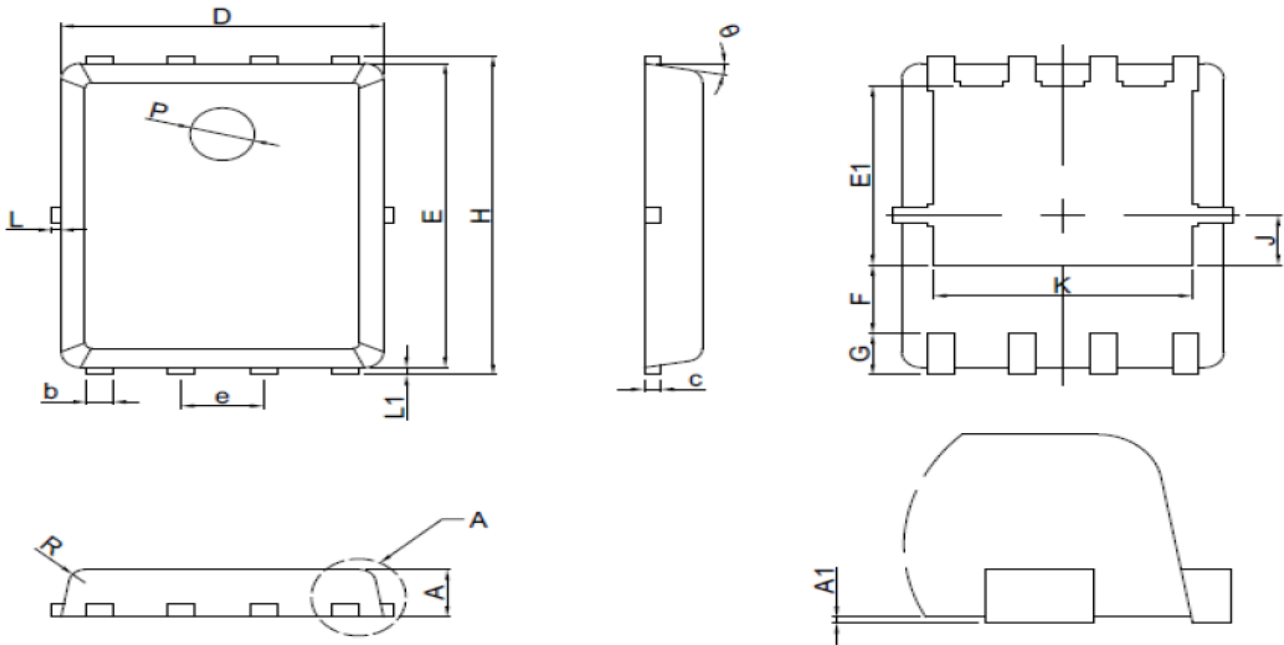
SYMBOL	MIN	NOM	MAX
A	4.40	4.50	4.60
A1	1.27	1.30	1.33
A2	2.30	2.40	2.50
b	0.70	0.60	0.90
b1	-	-	1.40
c	0.45	0.50	0.60
D	15.30	15.70	16.10
D1	9.10	9.20	9.30
D2	13.10	-	13.70
E	9.70	9.90	10.20
E1	7.80	8.00	8.20
e	2.54BSC		
e1	5.08BSC		
H1	6.30	6.50	6.70
L	12.78	13.08	13.38
L1	-	-	3.50
L2	4.6REF		
$\phi P$	3.55	3.60	3.65
Q	2.73	-	2.87
$\theta 1$	1°	3°	5°



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### PPAK5x6-8L PACKAGE OUTLINE



SYMBOL	MILLIMETERS		
	MIN	NOM	MAX
A	0.8	0.95	1.1
A1	0.00	0.03	0.05
b	0.33	0.41	0.51
c	0.254 REF		
D	4.80	4.95	5.10
F	1.40 REF		
E	5.70	5.80	5.90
e	1.27 BSC		
H	5.90	6.05	6.20
L1	0.06	0.13	0.20
G	0.60 REF		
J	0.95 BSC		
K	4.00 REF		
L	---	----	0.20
P	1.00 REF		
E1	3.40REF		
E2	0.95 REF		
$\theta$	6°	10°	14°
R	0.25REF		

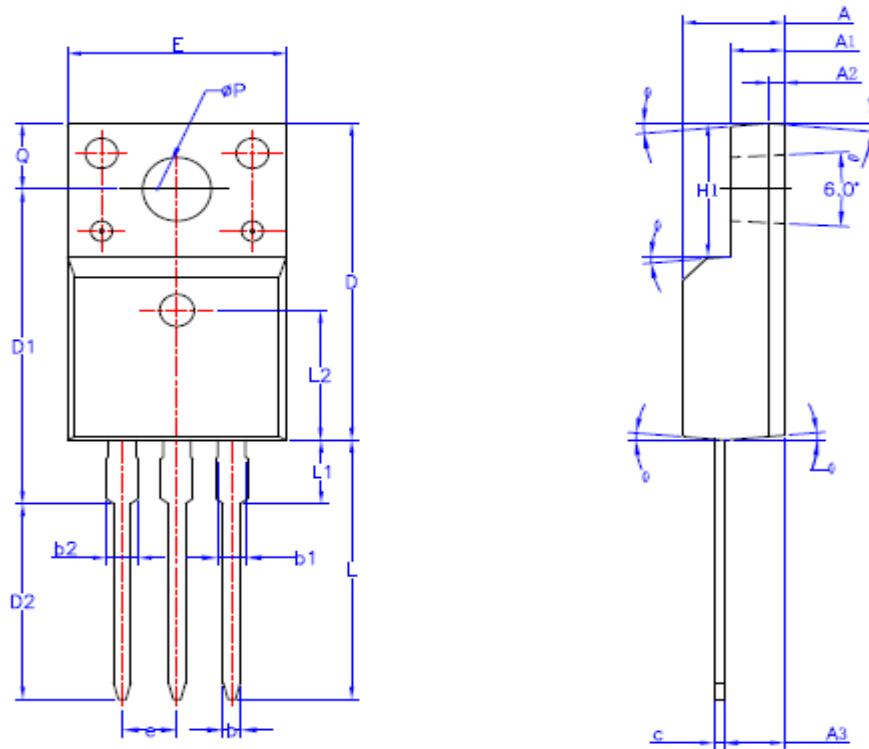




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### TO-220F-3L PACKAGE OUTLINE



SYMBOL	MIN	NOM	MAX
A	4.50	4.70	4.83
A1	2.34	2.54	2.74
A2	0.7REF		
A3	2.56	2.76	2.93
b	0.70	--	0.90
b1	1.18	--	1.40
b2	--	--	1.47
c	0.45	0.50	0.60
D	15.67	15.87	16.07
D1	15.55	15.75	15.95
D2	9.60	9.80	10.00
E	9.96	10.16	10.36
e	2.54BSC		
H1	6.48	6.68	6.88
L	12.68	12.98	13.28
L1	-	-	3.50
L2	6.50REF		
$\phi P$	3.08	3.18	3.28
Q	3.20	-	3.40
$\theta$ 1	1°	3°	5°



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